

**INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION  
(PTO-1449)**

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APPLICANT  
**Kenji WATANABE et al**

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1792

**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

/G.N.R./	Shojiro Komatsu, September 24, 2002; Vol 63, No. 1, Page 116 (26p-D-3), PLD PURAZUMAASHISUTEDO modulation method (MPA-PLD) from sp3-bonded 5H-BN of 225nm ultraviolet light emitting
/G.N.R./	A new Flux for Growing Hexagonal Boron Nitride Crystals at Low Temperature, page L300 to L302, Masaichi yano et al; February 14, 2000
/G.N.R./	Growth of Single Crystals of Hexagonal Boron Nitride; Journal of Crystal Growth 61 (1983) 689 to 690; North-Holland Publishing company; T. Ishii and T. Sato
EXAMINER /G. Nagesh Rao/ (05/26/2009)	DATE CONSIDERED 05/26/2009

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